

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	271	438/620.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 12:03
L2	1044	438/612.ccls. and wire	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 11:41
L3	6	("5091346"   "5287620"   "5314709"   "5561622"   "5683529"   "6013713"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/26 11:46
L4	2	("6077727").PN. OR ("6372620"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/26 11:49
L5	7	"438"/\$.ccls. and active adj "substrates" and passive adj substrates	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 12:06
L6	0	plurality near2 active adj "substrates" and passive adj substrates	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 12:07
L7	2	plurality near5 active adj "substrates" and passive adj substrates	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 12:08
L8	10	"active" adj "substrates" and passive adj substrates and bonding adj pad	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 12:15
L9	31	active adj substrates and passive adj substrates and pad and wire	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 12:53
L10	21	plurality adj substrates near5 (transistors or diodes) and substrate near5 ("si" or silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 12:57
L11	7485	substrates near5 comprising near5 (transistors or diodes) and substrate near5 ("si" or silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 13:02
L12	6166	substrates near5 comprising near5 (transistors or diodes) and substrate near5 ("si" or silicon) and "257"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 13:03

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L13	1	substrates near5 comprising near5 (transistors or diodes) and substrate near5 ("si" or silicon) and "257"/\$.ccls.	JPO	OR	ON	2006/04/26 13:03
L14	0	substrates near5 comprising near5 (transistors or diodes) and substrate near5 ("si" or silicon) and "257"/\$.ccls.	IBM_TDB	OR	ON	2006/04/26 13:03
L15	0	substrates near5 comprising near5 (transistors or diodes) and substrate near5 ("si" or silicon) and "257"/\$.ccls.	DERWENT	OR	ON	2006/04/26 13:03
L16	15	substrates near5 comprising near5 (transistors or diodes) and substrate near5 ("si" or silicon) and "257"/\$.ccls.	EPO	OR	ON	2006/04/26 13:04
L17	13	"substrates" near5 comprising near5 (transistors or diodes) and "substrate" near5 ("si" or silicon) and "257"/\$.ccls.	USPAT	OR	OFF	2006/04/26 13:05
L18	5	"substrates" near5 comprising near5 (transistors or diodes) and "substrate" near5 ("si" or silicon) and "257"/\$.ccls.	US-PGPUB	OR	OFF	2006/04/26 13:45
L19	2139691	wire adj bonding near3 within substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 13:47
L20	11	wire adj bonding near3 within near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 14:51
L21	908	257/379.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 14:59
L22	189	257/516.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 15:03
L23	486	257/528.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 15:09
L24	2	("6642617").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/04/26 15:03
L25	2299	257/723.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 15:20

## EAST Search History

L26	797	257/782.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 15:27
L27	2152	257/784.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 15:30
L28	3745	257/787.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/26 15:30